L Number	Hits	Search Text	DB	Time stamp
8	2207	((427/240) or (118/52) or (427/425) or (118/320)).CCLS.	USPAT;	2004/05/23 20:58
		((12)/2/07/07/07/07/07/07/07/07/07/07/07/07/07/	US-PGPUB	
9	61	(((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer	USPAT;	2004/05/23 21:05
1	•	and (heat\$3 same inert)	US-PGPUB	200 003/25 21:03
10	27	((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer	USPAT;	2004/05/23 20:59
1		and (heat\$3 same inert)) and @ad<19980320	US-PGPUB	200 (105/25 20.5)
11	8	(((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer	USPAT;	2004/05/23 20:59
**	Ü	and (heat\$3 same inert)) and @ad<19980320) and oxidiz\$3	US-PGPUB	2004/03/23 20.37
12	921	semiconductor and wafer and (heat\$3 same inert) and oxidiz\$3 and	USPAT;	2004/05/23 21:05
**	721	@ad<19980320 not ((((((427/240) or (118/52) or (427/425) or	US-PGPUB	2004/03/23 21:03
		(118/320)).CCLS.) and wafer and (heat\$3 same inert)) and	05-1 GI 0B	
		(170/320)). 300 mile water and (16003) state merty) and (219980320) and oxidiz\$3)		
13	237	semiconductor and wafer and ((heat\$3 same inert) same oxidiz\$3) and	USPAT;	2004/05/23 21:24
1.5	231	@ad<19980320 not ((((((427/240) or (118/52) or (427/425) or	US-PGPUB	2004/03/23 21.24
		(118/320)).CCLS.) and wafer and (heat\$3 same inert)) and	03-1 01 015	
		(110/320)), CCES; and water and (10/33) same mercy and (20/320) and oxidiz\$3)		
14	51	semiconductor and wafer ab. and ((heat\$3 same inert) same oxidiz\$3)	USPAT;	2004/05/23 21:24
17	31	and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or	US-PGPUB	2004/03/23 21.24
		(118/320)).CCLS.) and wafer and (heat\$3 same inert)) and	05-1 GI OD	
		(110/320)).0025.) and water and (10005 same merty) and (21980320) and oxidiz\$3)		
15	3	semiconductor and wafer ab. and ((heat\$3 same inert) same	USPAT;	2004/05/23 21:06
] * ]	3	oxidiz\$3).ab. and @ad<19980320 not (((((427/240) or (118/52) or	US-PGPUB	2004/03/23 21:00
		(427/425) or (118/320)). CCLS.) and wafer and (heat\$3 same inert)) and	05-1 01 01	
		@ad<19980320) and oxidiz\$3)		
16	16	(semiconductor and wafer ab. and ((heat\$3 same inert) same oxidiz\$3)	USPAT;	2004/05/23 21:07
10	10	and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or	US-PGPUB	200 1703723 21.07
1		(118/320)).CCLS.) and wafer and (heat\$3 same inert)) and	0010100	
j		@ad<19980320) and oxidiz\$3)) and (coat\$3 same heat\$3)		
17	29	semiconductor and wafer and ((heat\$3 same inert) same oxidiz\$3 same	USPAT;	2004/05/23 21:24
- '		coat\$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425)	US-PGPUB	200 11 02/25 27.21
		or (118/320)).CCLS.) and wafer and (heat\$3 same inert)) and	00.00	
		@ad<19980320) and oxidiz\$3)		
18	21	(semiconductor and wafer and ((heat\$3 same inert) same oxidiz\$3 same	USPAT;	2004/05/23 21:42
		coat\$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425)	US-PGPUB	
		or (118/320)).CCLS.) and wafer and (heat\$3 same inert)) and		
		@ad<19980320) and oxidiz\$3)) not ((semiconductor and wafer ab. and		
		((heat\$3 same inert) same oxidiz\$3) and @ad<19980320 not		
		((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer		
		and (heat\$3 same inert)) and @ad<19980320) and oxidiz\$3)) and		
		(coat\$3 same heat\$3))		
20	276	(semiconductor adj wafer) and (((hot or heat or heating) adj plate) same	USPAT;	2004/05/23 21:44
		pin)	US-PGPUB	
21	99	(semiconductor adj wafer) and (((hot or heat or heating) adj plate) same	USPAT;	2004/05/23 21:56
		pin) and inert	US-PGPUB	
22	14	((semiconductor adj wafer) and (((hot or heat or heating) adj plate) same	USPAT;	2004/05/23 21:44
		pin) and inert) and @ad<19980320	US-PGPUB	
23	0	(wafer) and (((hot or heat or heating) adj plate) same pin) and inert and	USPAT;	2004/05/23 21:56
		@ad<19980320 not (((semiconductor adj wafer) and (((hot or heat or	US-PGPUB	
		heating) adj plate) same pin) and inert) and @ad<19980320)		